RENESAS

MOS FIELD EFFECT TRANSISTOR 2SK4213A

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK4213A is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

FEATURES

Low on-state resistance

 $\begin{aligned} R_{DS(on)1} &= 6.0 \text{ m}\Omega \text{ MAX. } (V_{GS} = 10 \text{ V}, \text{ I}_{D} = 30 \text{ A}) \\ R_{DS(on)2} &= 9.5 \text{ m}\Omega \text{ MAX. } (V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}) \end{aligned}$

Low total gate charge

Qg = 34 nC TYP. (VDD = 15 V, VGS = 10 V, ID = 30 A)

- 4.5 V drive available
- Avalanche capability ratings

ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE	
2SK4213A-ZK-E1-AY Note	Duro Cn (Tin)	Tape 2500 p/reel		
2SK4213A-ZK-E2-AY Note	K4213A-ZK-E2-AY ^{Note} Pure Sn (Tin)		TO-252 (MP-3ZK) typ. 0.27 g	

Note Pb-free (This product does not contain Pb in external electrode).

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	30	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C)	ID(DC)	±64	А
Drain Current (pulse) Note1	D(pulse)	±175	А
Total Power Dissipation (Tc = 25°C)	P T1	45	W
Total Power Dissipation (T _A = 25°C)	Pt2	1.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note2	las	20	А
Single Avalanche Energy ^{Note2}	Eas	40	mJ

(TO-252)



Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Starting T_{ch} = 25°C, V_{DD} = 15 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V, L = 0.1 mH

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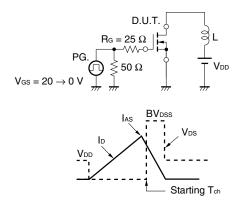
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	lgss	V _{GS} = ±16 V, V _{DS} = 0 V			±100	nA
Gate to Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.5		3.0	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 5 V, I _D = 16 A	12	24		S
Drain to Source On-state Resistance ^{Note}	RDS(on)1	Vgs = 10 V, Id = 30 A		5.3	6.0	mΩ
	RDS(on)2	Vgs = 4.5 V, Id = 20 A		7.4	9.5	mΩ
Input Capacitance	Ciss	V _{DS} = 15 V,		1700		pF
Output Capacitance	Coss	V _{GS} = 0 V,		240		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		130		pF
Turn-on Delay Time	t _{d(on)}	Vdd = 15 V, Id = 30 A,		17		ns
Rise Time	tr	V _{GS} = 10 V,		17		ns
Turn-off Delay Time	t _{d(off)}	Rg = 3 Ω		57		ns
Fall Time	tr			7		ns
Total Gate Charge	QG	V _{DD} = 15 V,		34		nC
Gate to Source Charge	Q _{GS}	Vgs = 10 V,		5		nC
Gate to Drain Charge	Qgd	ID = 30 A		9		nC
Body Diode Forward Voltage Note	VF(S-D)	IF = 30 A, VGS = 0 V		0.86	1.5	V
Reverse Recovery Time	trr	IF = 30 A, VGS = 0 V,		24		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/ <i>µ</i> s		15		nC

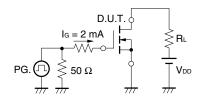
Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

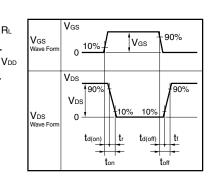
TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE



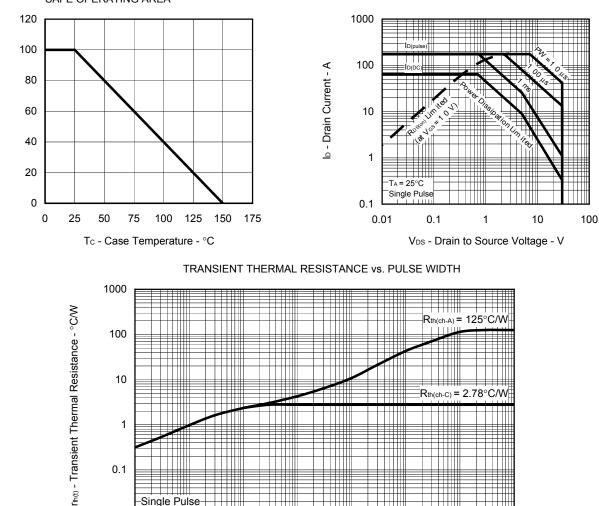
 $PG. \xrightarrow{P}_{R_{G}} \xrightarrow{R_{G}} \xrightarrow{P}_{M_{T}} \xrightarrow{P$



dT - Percentage of Rated Power - %



FORWARD BIAS SAFE OPERATING AREA



1

100 m

PW - Pulse Width - s

V_{GS(th)} - Gate to Source Threshold Voltage - V

10 m

10



Single Pulse

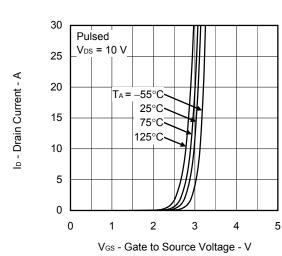
1 m

10

1

0.1

0.01 100 *µ*



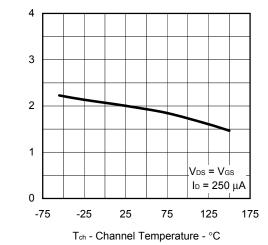
GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE

1000

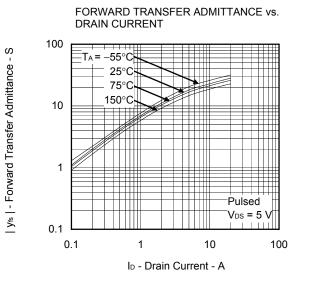
Rth(ch-C) = 2.78°C/W

Т

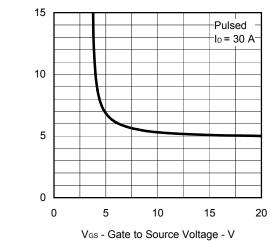
100



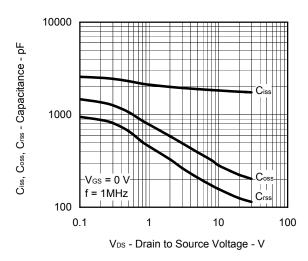
Data Sheet D20286EJ1V0DS



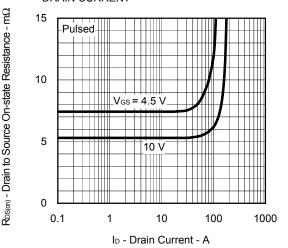
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



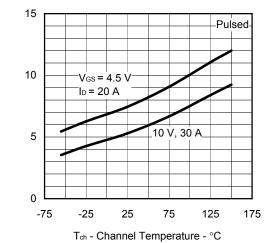
CAPACITANCE vs. DRAIN TOSOURCE VOLTAGE



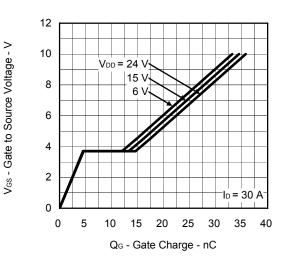
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



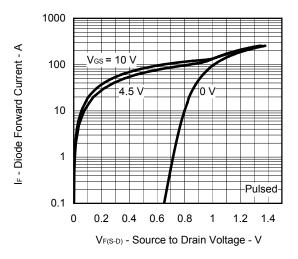
DYNAMIC INPUT CHARACTERISTICS



 $R_{DS(m)}$ - Drain to Source On-state Resistance - $m\Omega$

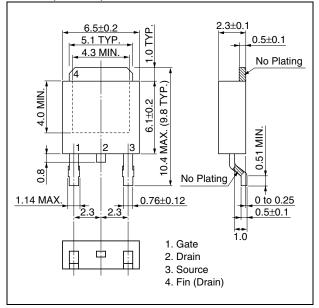
 $R_{DS(on)}$ - Drain to Source On-state Resistance - $m\Omega$

SOURCE TO DRAIN DIODE FORWARD VOLTAGE

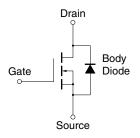


PACKAGE DRAWINGS (Unit: mm)

TO-252 (MP-3ZK)



EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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